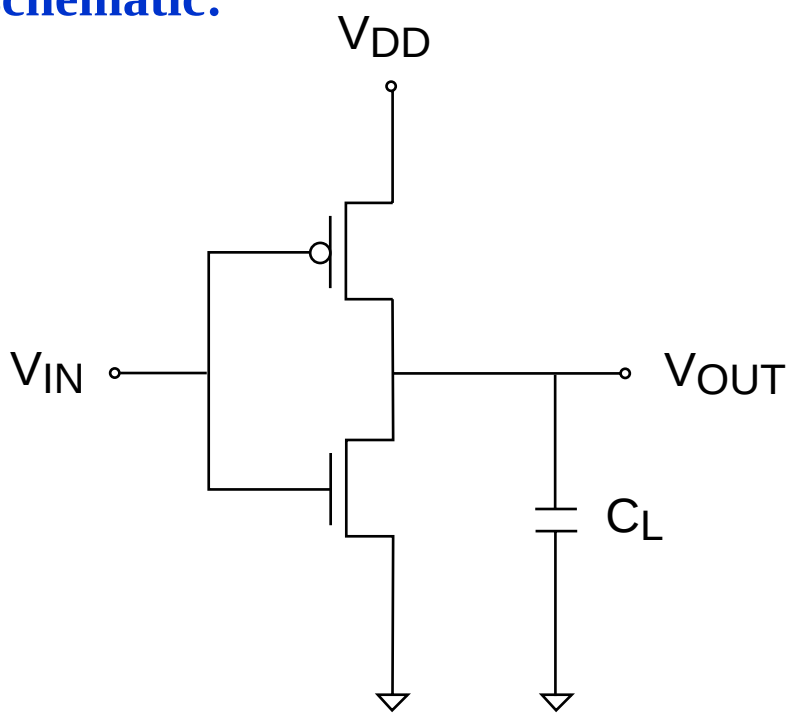
Lecture 13
Circuits numériques (III)
Circuits CMOS

Outline

- CMOS Inverter: **Propagation Delay**
- CMOS Inverter: **Power Dissipation**
- CMOS: **Static Logic Gates**

1. Complementary MOS (CMOS) Inverter

Circuit schematic:



Basic Operation:

- $V_{IN} = 0 \Rightarrow V_{OUT} = V_{DD}$
  - $V_{GSn} = 0$ ($< V_{Tn}$) $\Rightarrow$ **NMOS OFF**
  - $V_{SGp} = V_{DD}$ ($> -V_{Tp}$) $\Rightarrow$ **PMOS ON**
- $V_{IN} = V_{DD} \Rightarrow V_{OUT} = 0$
  - $V_{GSn} = V_{DD}$ ($> V_{Tn}$) $\Rightarrow$ **NMOS ON**
  - $V_{SGp} = 0$ ($< -V_{Tp}$) $\Rightarrow$ **PMOS OFF**

No power consumption while idle in any logic state!

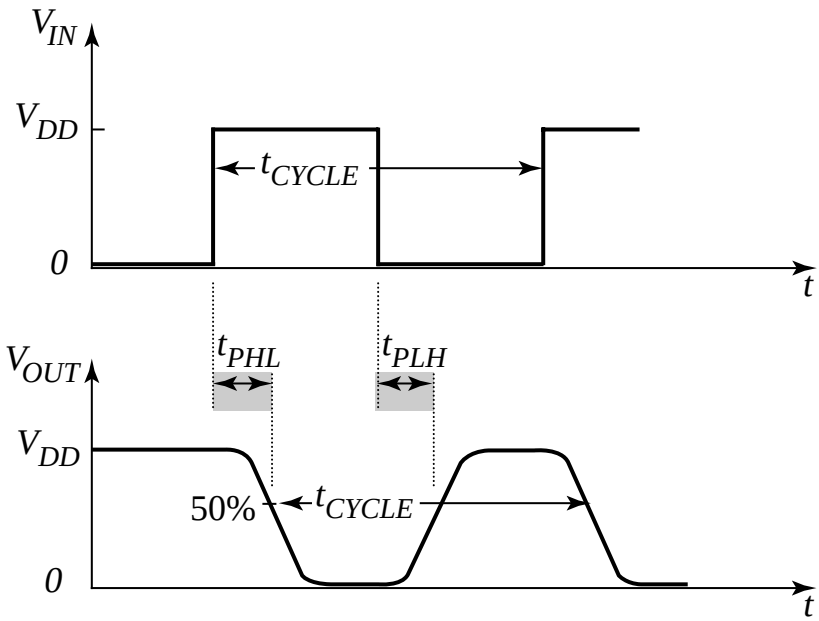
2. CMOS inverter: Propagation delay

Inverter propagation delay: time delay between input and output signals; figure of merit of logic speed.

Typical propagation delays: < 100 ps.

- Complex logic system has 10-50 propagation delays per clock cycle.

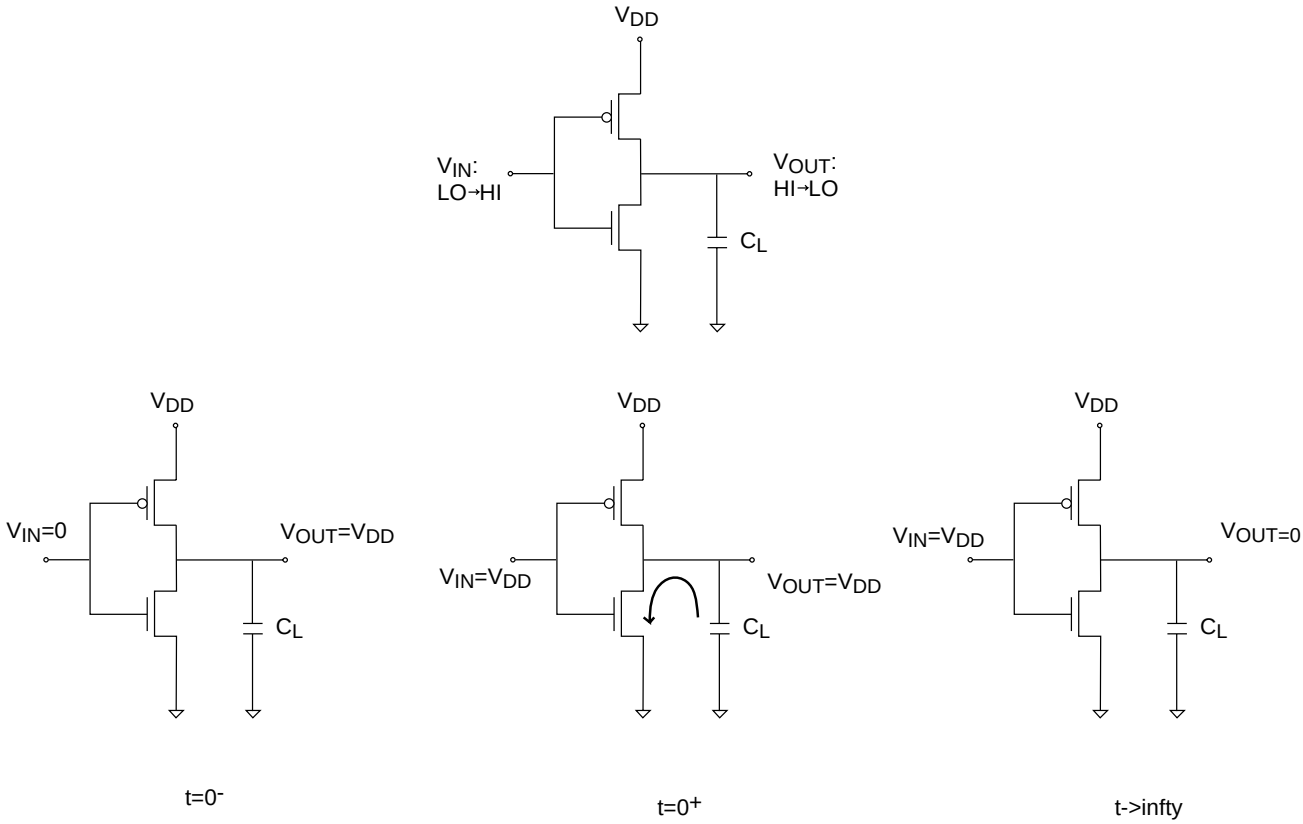
Estimation of t_p: use square-wave at input



Average propagation delay:

$$\mathbf{t_p = \frac{1}{2}\left(t_{PHL} + t_{PLH}\right)}$$

CMOS inverter:
Propagation delay high-to-low



During early phases of discharge, NMOS is saturated and PMOS is cut-off.

Time to discharge ***half*** of charge stored in C_L:.

$$t_{pHL} \approx \frac{\frac{1}{2}\text{charge on } C_L \ @t = 0^-}{\text{NMOS discharge current}}$$

CMOS inverter:
Propagation delay high-to-low (contd.)

Charge in C_L at $t=0^-$:

$$Q_L\left(t=0^-\right)=C_L V_{DD}$$

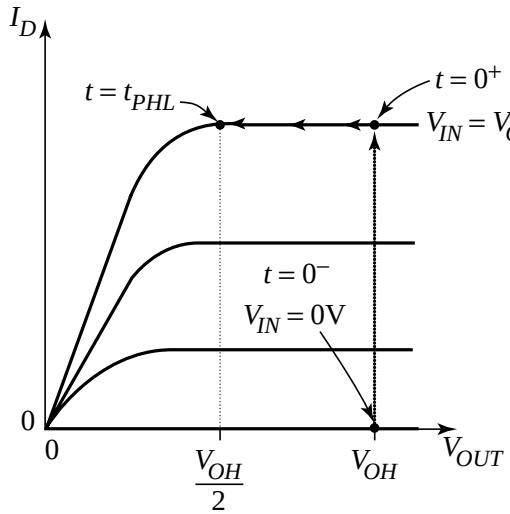
Discharge Current (NMOS in saturation):

$$I_{Dn}=\frac{W_n}{2L_n}\mu_n C_{ox}\left(V_{DD}-V_{Tn}\right)^2$$

Then:

$$t_{PHL}\approx\frac{C_L V_{DD}}{\frac{W_n}{L_n}\mu_n C_{ox}\left(V_{DD}-V_{Tn}\right)^2}$$

Graphical Interpretation



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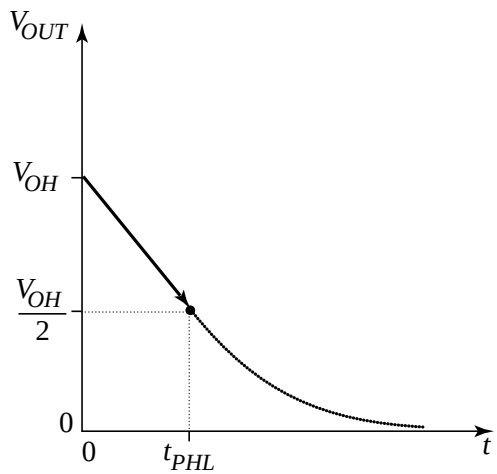

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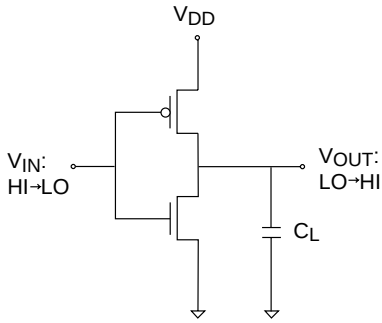
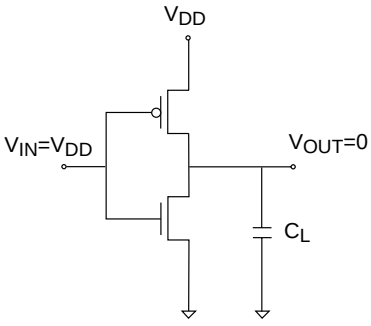
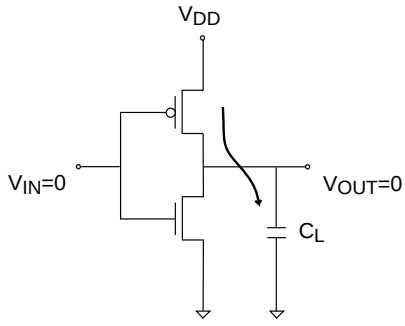
CMOS inverter:
Propagation delay low-to-high

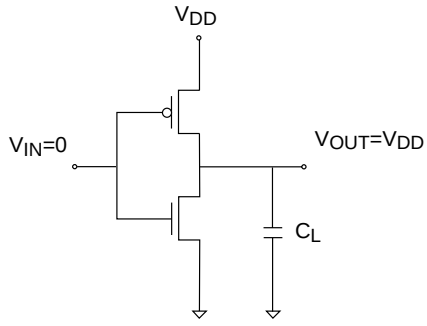




t=0-



t=0+



t->infty

During early phases of discharge, PMOS is saturated and NMOS is cut-off.

Time to charge to ***half*** of final charge on C_L:.

$$t_{PLH} \approx \frac{\frac{1}{2}\text{charge on } C_L \ @t=\infty}{\text{PMOS charge current}}$$

CMOS inverter:
Propagation delay high-to-low (contd.)

Charge in C_L at $t=\infty$:

$$\mathbf{Q_L(t=\infty) = C_L V_{DD}}$$

Charge Current (PMOS in saturation):

$$\mathbf{-I_{Dp} = \frac{W_p}{2L_p}\mu_p C_{ox}\left(V_{DD} + V_{Tp}\right)^2}$$

Then:

$$\mathbf{t_{PLH} \approx \frac{C_L V_{DD}}{\frac{W_p}{L_p}\mu_p C_{ox}\left(V_{DD} + V_{Tp}\right)^2}}$$

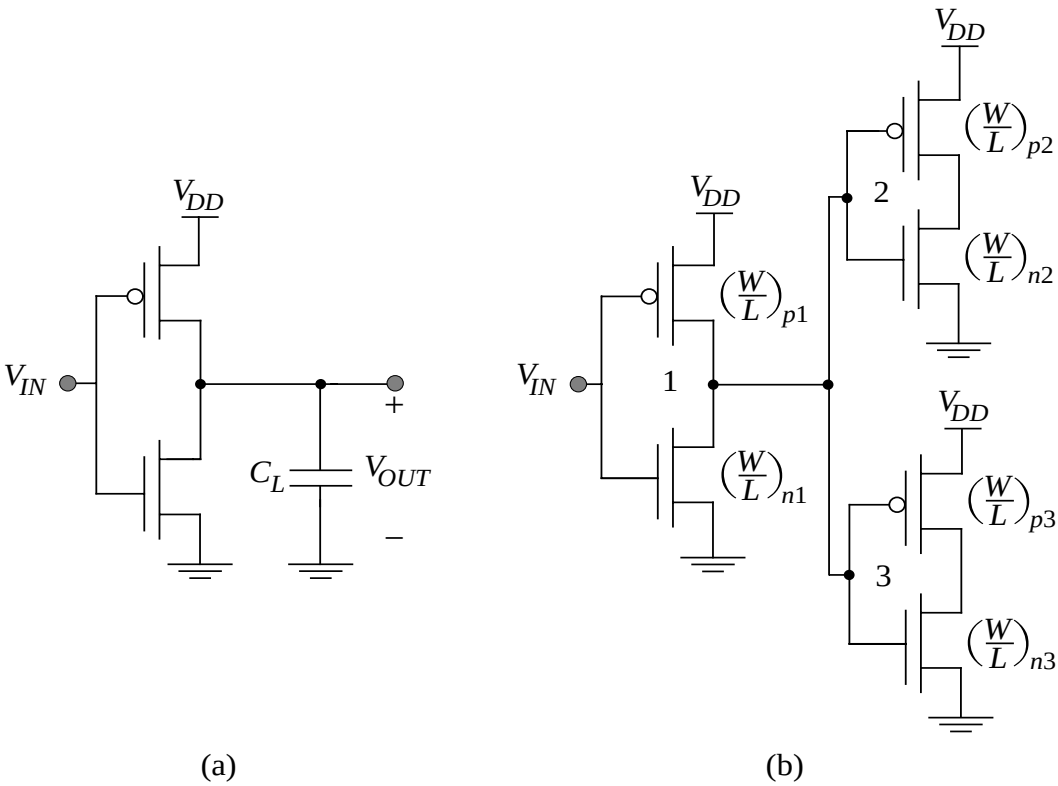
Key dependencies of propagation delay:

- $V_{DD} \uparrow \Rightarrow t_p \downarrow$
  - Reason: $V_{DD} \uparrow \Rightarrow Q(C_L) \uparrow$, but I_D goes as square$\uparrow$
  - Trade-off: $V_{DD} \uparrow \Rightarrow$ more power consumed.
- $L \downarrow \Rightarrow t_p \downarrow$
  - Reason: $L \downarrow \Rightarrow I_D \uparrow$
  - Trade-off: manufacturing cost!

Components of load capacitance C_L:

- ***Following logic gates***: must add capacitance of each gate of every transistor the output is connected to.
- ***Interconnect wires*** that connects output to input of following logic gates
- ***Own drain-to-body capacitances***

$$C_L = C_G + C_{wire} + C_{DBn} + C_{DBp}$$



Gate Capacitance of Next Stage

- Estimation of the input capacitance:
  - n- and p-channel transistors in the next stage switch from triode through saturation to cutoff during a high-low or low-high transition

- Requires nonlinear charge storage elements to accurately model

- Hand Calculation use a rough estimate for an inverter

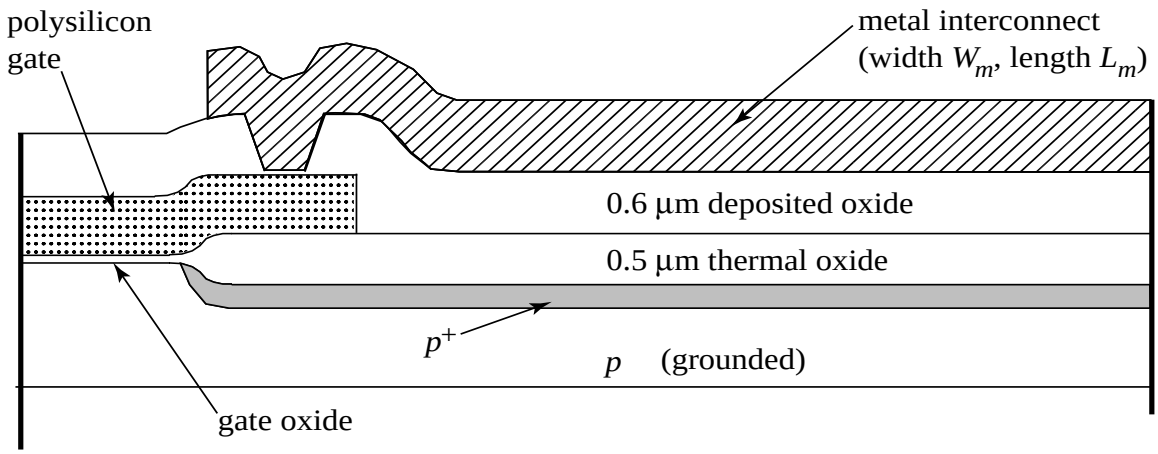
$$C_{in} = C_{ox}(WL)_p + C_{ox}(WL)_n$$

CG for example circuit

$$C_G = C_{ox}(WL)_{p2} + C_{ox}(WL)_{n2} + C_{ox}(WL)_{p3} + C_{ox}(WL)_{n3}$$

Interconnect Capacitance

• "Wires" consist of metal lines connecting the output of the inverter to the input of the next stage



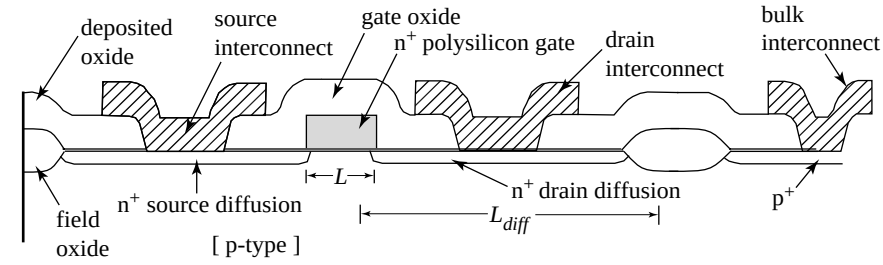
• The p+ layer (i.e., heavily doped with acceptors) under the thick thermal oxide (500 nm = 0.5 mm) and deposited oxide (600 nm = 0.6 mm) depletes only slightly when positive voltages appear on the metal line, so the capacitance is approximately the oxide capacitance:

$$\mathbf{C_{wire} = C_{thickox}\,(W_m * L_m)}$$

where the oxide thickness = 500 nm + 600 nm = 1.1 µm.

For large digital systems, the parasitic wiring capacitance can dominate the load capacitance

Parasitic Capacitance-Drain/Bulk Depletion



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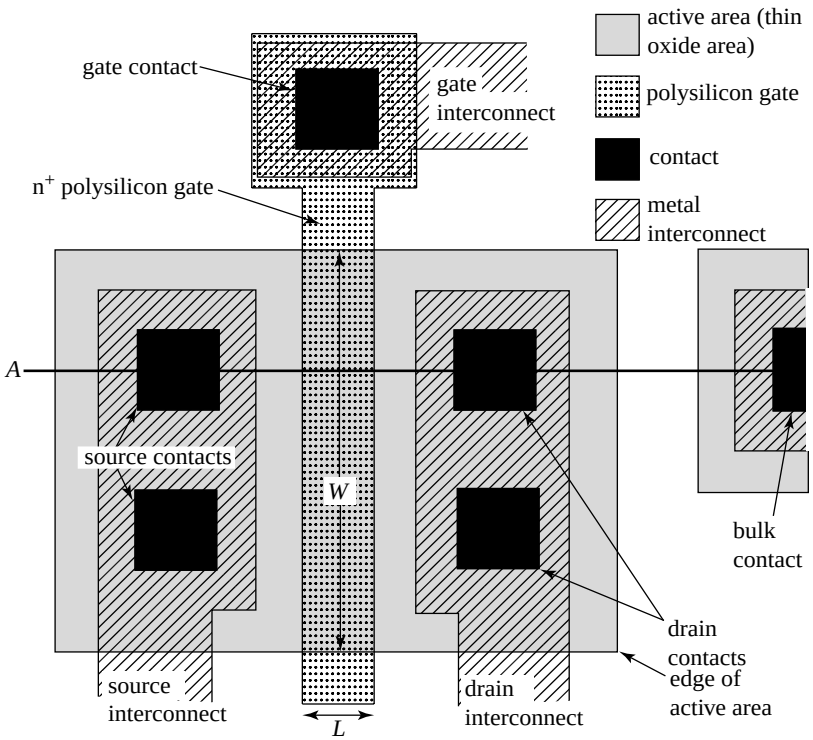

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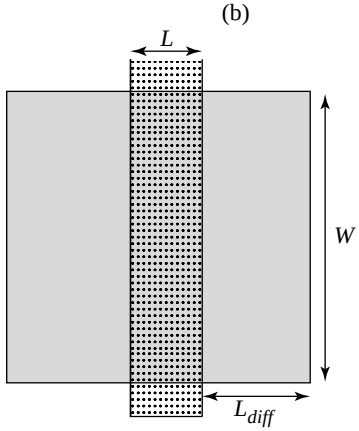


(c)

Calculation of Parasitic Drain/Bulk Junction Depletion Capacitance

• Depletion $q_J(v_D)$ is non-linear --> take the worst case and use the zero-bias capacitance C_{jo} as a linear charge-storage element during the transient.

• "Bottom" of depletion regions of the inverter's drain diffusions contribute a depletion capacitance:

$$\mathbf{C_{JBOT} = C_{Jn}(W_n L_{diffn}) + C_{Jp}(W_p L_{diffp})}$$

Where: C_{Jn} and C_{Jp} are the zero-bias bottom capacitance (fF/μm^2) for the n-channel and p-channel MOSFET drain-bulk junction, respectively.

Typical numbers: C_{Jn} and C_{Jp} are about 0.2 fF/μm^2

• "Sidewall" of depletion regions of the inverter's drain diffusions make an additional contribution:

$$\mathbf{C_{JSW} = (W_n + 2L_{diffn})C_{JSWn} + (W_p + 2L_{diffp})C_{JSWp}}$$

Where: C_{JSWn} and C_{JSWp} are the zero-bias sidewall capacitance (F/μm) for the n-channel and p-channel MOSFET drain-bulk junction, respectively.

Typical numbers: C_{JSWn} and C_{JSWp} are about 0.5 fF/μm

The sum of C_{JBOT} and C_{JSW} is the total depletion capacitance, C_{DB}

Power Dissipation

- Energy from power supply needed to charge up the capacitor:

$$E_{charge} = \int V_{DD} i(t) dt = V_{DD} Q = V_{DD}^2 C_L$$

- Energy stored in capacitor:

$$E_{store} = 1/2 C_L V_{DD}^2$$

- Energy lost in p-channel MOSFET during charging:

$$E_{diss} = E_{charge} - E_{store} = 1/2 C_L V_{DD}^2$$

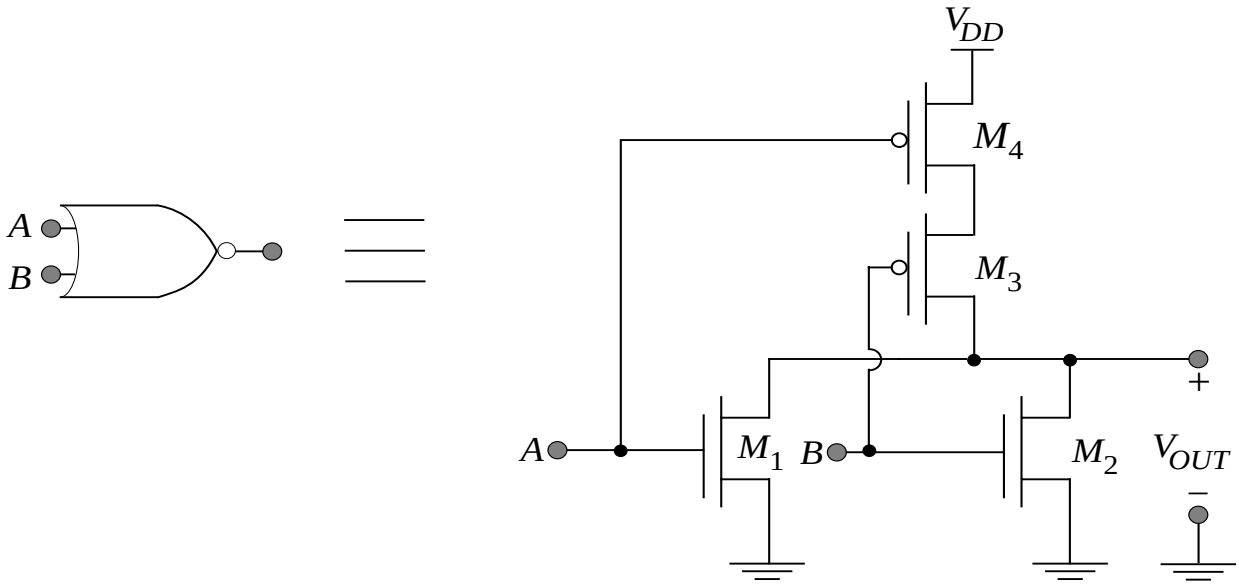
•During discharge the n-channel MOSFET dissipates an identical amount of energy.

•If the charge/discharge cycle is repeated f times/second, where f is the clock frequency, the dynamic power dissipation is:

$$P = 2 E_{diss} * f = C_L V_{DD}^2 f$$

In practice many gates do not change state every clock cycle which lowers the power dissipation.

CMOS Static Logic Gates



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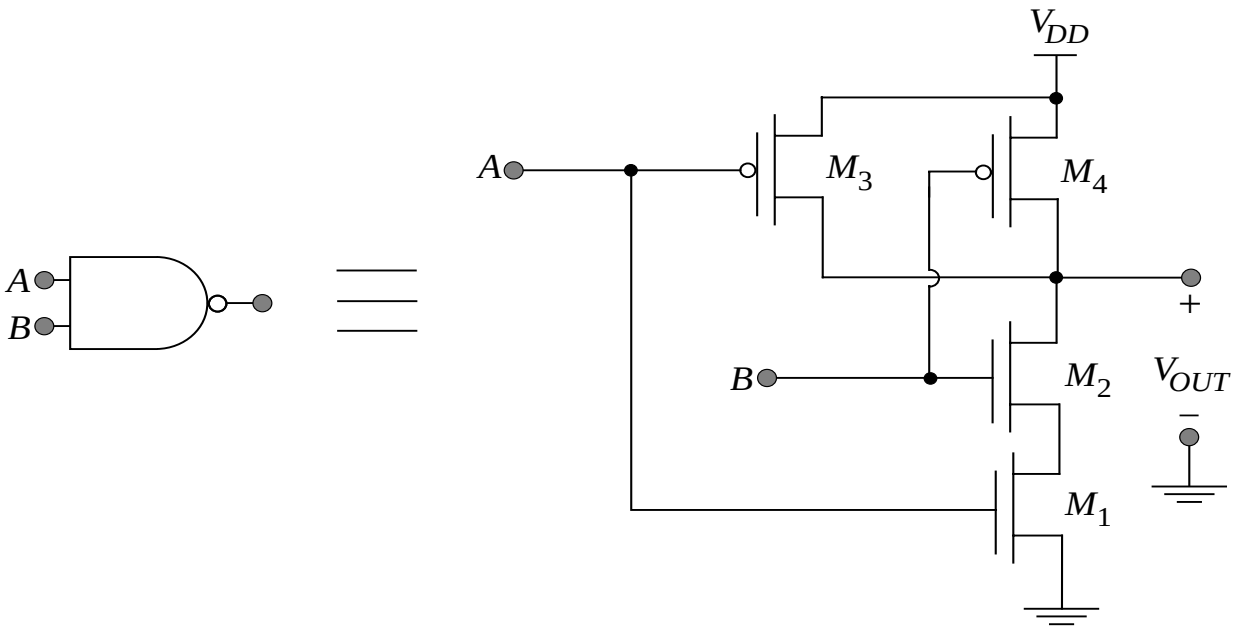

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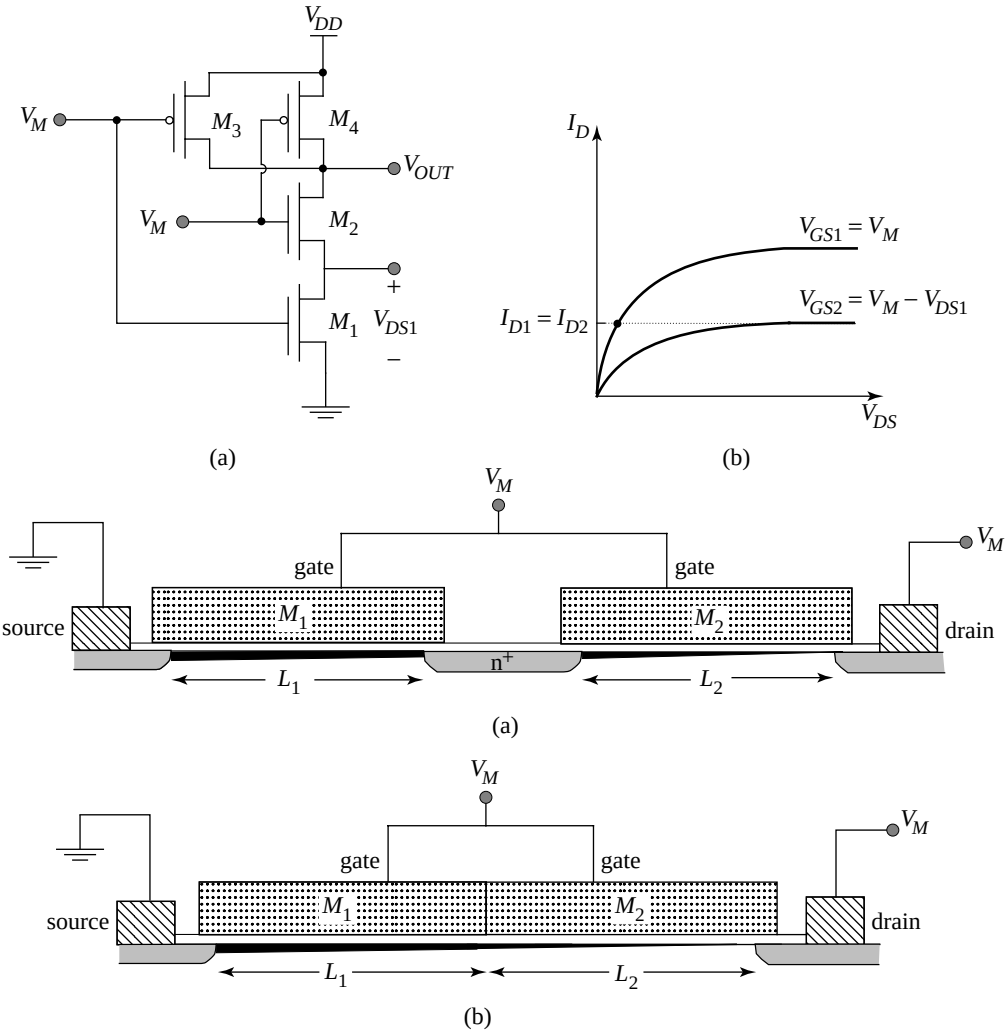
CMOS NAND Gate

I-V Characteristics of n-channel devices



- Effective length of two n-channel devices is $2L_n$
  - $K_{neff} = k_{n1}/2 = k_{n2}/2$ Recall $k_n = W/L\mu_n C_{ox}$

- Effective width of two p-channel devices is $2W_p$ BUT worst case only one device is on
  - $K_{peff} = k_{p3} = k_{p4}$

Calculation of static and transient performance for NAND Gate

- $k_{peff} = k_{neff}$ is desirable for equal propagation delays and symmetrical transfer characteristics
- If $\mu_n = 2\mu_p$
- Therefore $(W/L)_n = (W/L)_p$

  for 2-input NAND gate

- In general for an M-input NAND Gate

$$\left(\frac{W}{L}\right)_n = \frac{M}{2}\left(\frac{W}{L}\right)_p$$

What did we learn today?

Summary of Key Concepts

Key features of CMOS inverter:

- No current between power supply and ground while inverter is idle in any logic state
- "rail-to-rail" logic
  - Logic levels are 0 and V_{DD}.
- High $|A_v|$ around the logic threshold
  - $\Rightarrow$ Good noise margins.

CMOS inverter logic threshold and noise margins engineered through W_n/L_n and W_p/L_p.

Key dependencies of propagation delay:

- $V_{DD} \uparrow \Rightarrow t_p \downarrow$
- $L \downarrow \Rightarrow t_p \downarrow$

Power dissipation CV^2f

Sizing static gates